

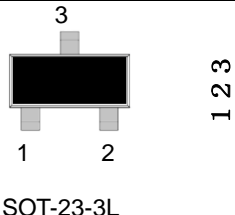

## 1、Description

Designed for use in solid state relays, MPU interface, TTL logic and any other light industrial or consumer application. Supplied in an inexpensive SOT-23-3L package which is readily adaptable for use in automatic insertion equipment. Sensitive Gate Triggering In Four Trigger Modes for all possible Combinations of Trigger Sources, and Especially for Circuits that Source Gate Drives

## 2、Features

- Blocking voltage to 600V
- On-state RMS current to 1.0 A
- Sensitive Gate Triggering In Four Trigger Modes (Quadrants) for all possible Combinations of Trigger Sources, and especially for Circuits that Source Gate Drives
- All Diffused and Glassivated Junctions for Maximum Uniformity of Parameters and Reliability
- Low cost package.

## 3、Pinning information

PIN	Description	Simplified outline	Symbol
1	main terminal 1(T1)		
2	Gate(G)		
3	main terminal 2(T2)		
		SOT-23-3L	

## 4、Quick reference data

SYMBOL	PARAMETER	MAX	UNIT
$V_{DRM}V_{RRM}$	Repetitive peak off-state voltages	600	V
$I_{T(RMS)}$	RMS on-state current	1.0	A
$I_{TSM}$	Non-repetitive peak on-state current	10	A

## 5、Thermal characteristics

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Thermal Resistance, Junction to Case	<i>in free air</i>	-	-	75	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	<i>in free air</i>	-	-	200	°C/W
$T_L$	Maximum Lead Temperature for Soldering Purposes for 10 Seconds	<i>in free air</i>	-	-	260	°C

## 6、Limiting value

Limiting values in accordance with the Maximum System(IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
$V_{DRM}, V_{RRM}$	Repetitive peak off-state voltages		-	-	600	V
$I_{T(RMS)}$	RMS on-state current	Full Cycle Sine Wave 50 to 60 Hz ( $T_C = +50\text{ }^{\circ}\text{C}$ )	-	-	1.0	A
$I_{TSM}$	Non-repetitive peak on-state current	One Full Cycle, Sine Wave 60 Hz ( $T_C = 110\text{ }^{\circ}\text{C}$ )	-	-	10	A
$I^2t$	$I^2t$ for fusing	$t = 8.3\text{ ms}$	-	-	0.26	$\text{A}^2\text{s}$
$I_{GM}$	Peak gate current		-	-	1.0	A
$V_{GM}$	Peak gate voltage		-	-	5.0	V
$P_{GM}$	Peak gate power		-	-	5.0	W
$P_{G(AV)}$	Average gate power	over any 20 ms period	-	-	0.5	W
$T_{stg}$	Storage temperature		-40	-	150	$^{\circ}\text{C}$
$T_j$	Operating junction temperature		-40	-	110	$^{\circ}\text{C}$

## 7、Characteristics

$T_J = 25^{\circ}\text{C}$  unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
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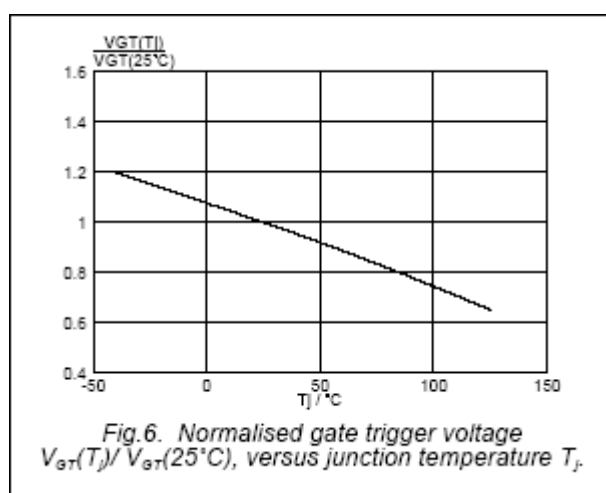
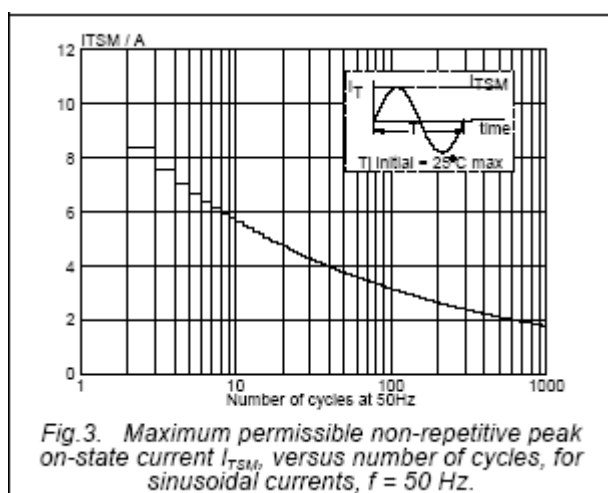
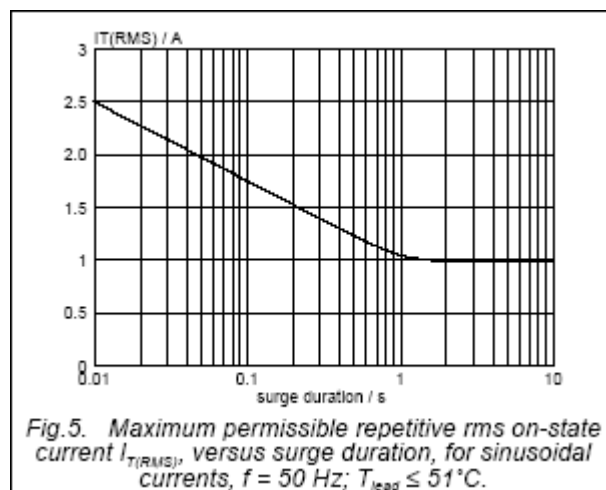
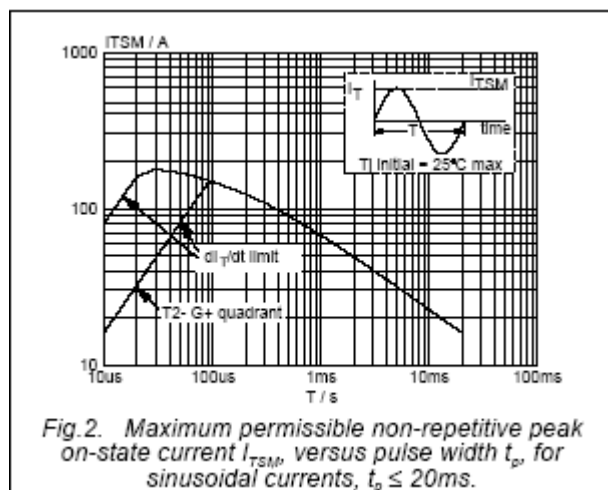
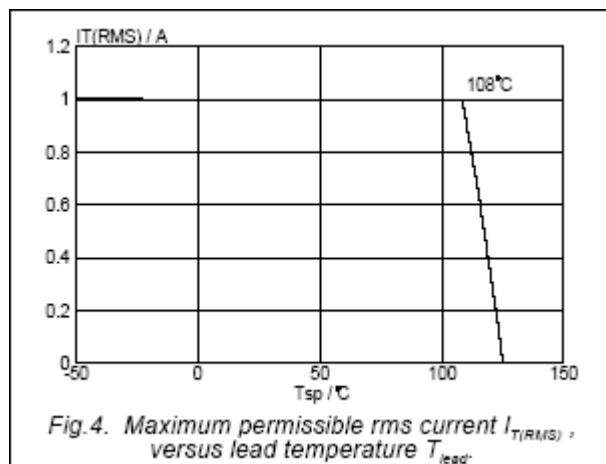
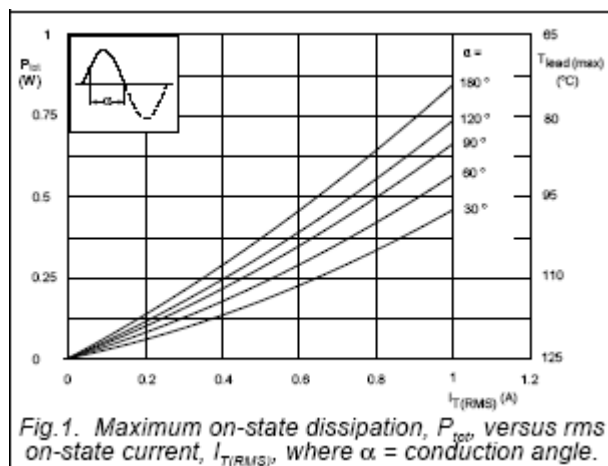
### Static characteristics

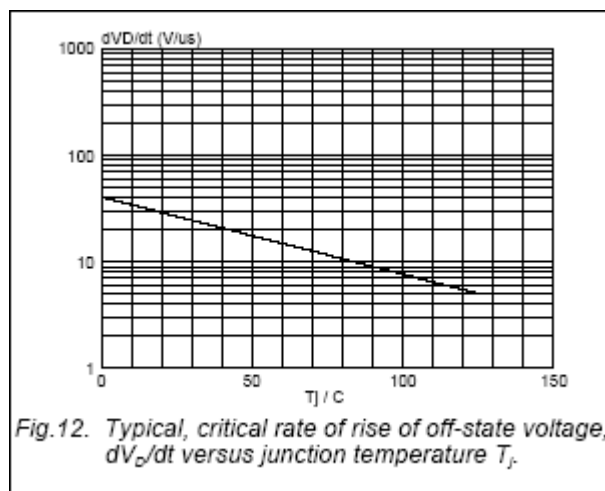
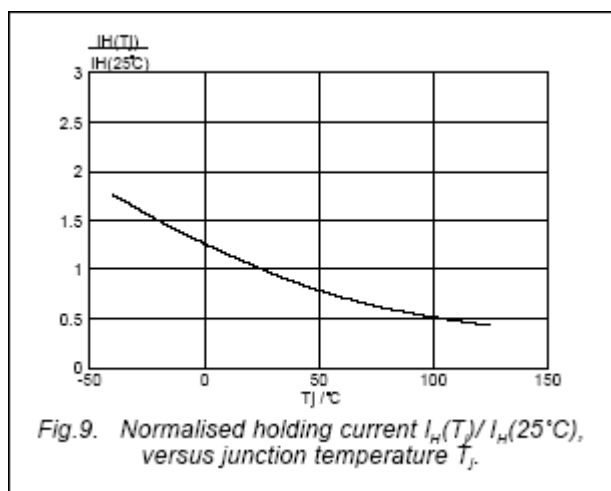
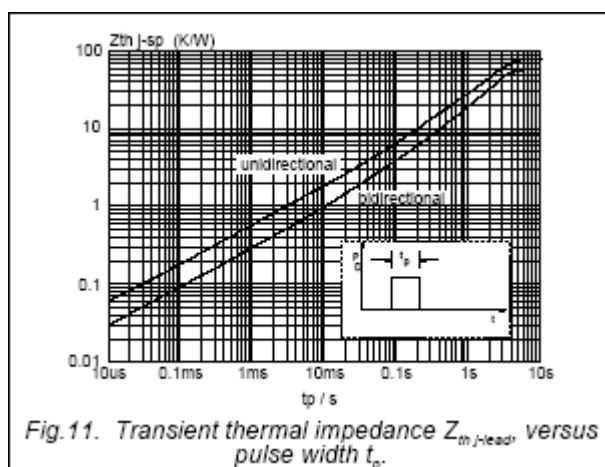
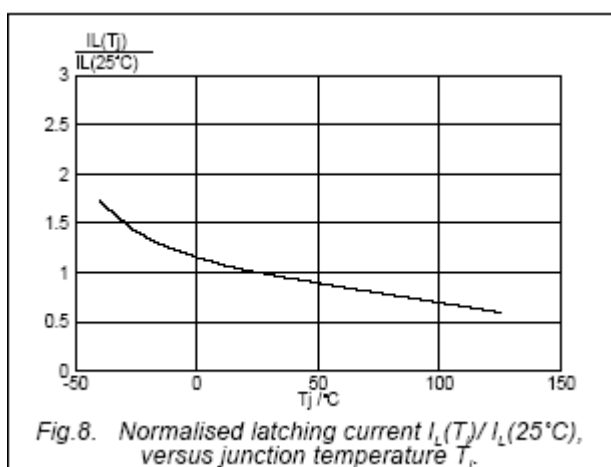
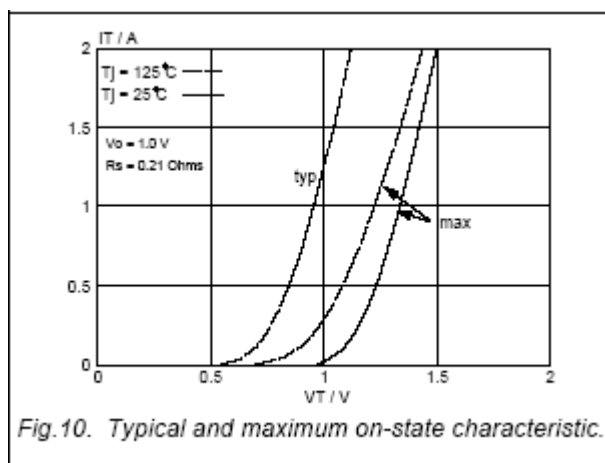
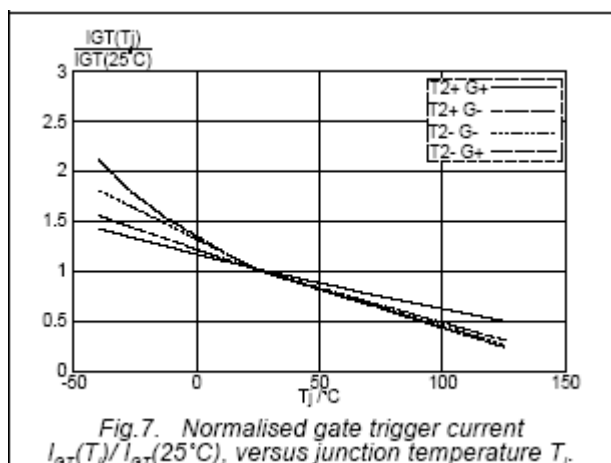
$I_{GT}$	Gate trigger current	( $V_D = 12\text{ Vdc}$ , $R_L = 100\text{ Ohms}$ )				
		T2+ G+	-	3	5	mA
		T2+ G-	-	3	5	mA
		T2- G-	-	3	5	mA
$I_L$	Latching current	( $V_D = 12\text{ V}$ ; $I_{GT} = 0.1\text{ A}$ )				
		T2+ G+	-	1.6	10	mA
		T2+ G-	-	10.5	20	mA
		T2- G-	-	1.5	15	mA
$I_H$	Holding current	( $V_D = 12\text{ V}$ ; Initiating Current = 200 mA, Gate Open)				
		T2+ G+	-	1.5	10	mA
		T2+ G-	-	1.5	10	mA
		T2- G-	-	1.5	10	mA
$V_{GT}$	Gate trigger voltage	( $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ )				
		T2+ G+	-	0.66	2.0	V
		T2+ G-	-	0.77	2.0	V
		T2- G-	-	0.84	2.0	V
$V_{GD}$	Off-state leakage Voltage	( $V_D = 12\text{ V}$ , $R_L = 100\text{ Ohms}$ , $T_J = 110\text{ }^{\circ}\text{C}$ ; All Four Quadrants)				
		T2+ G+	-	0.88	2.5	V
		T2+ G-	-	0.88	2.5	V
		T2- G-	-	0.88	2.5	V

### Dynamic Characteristics

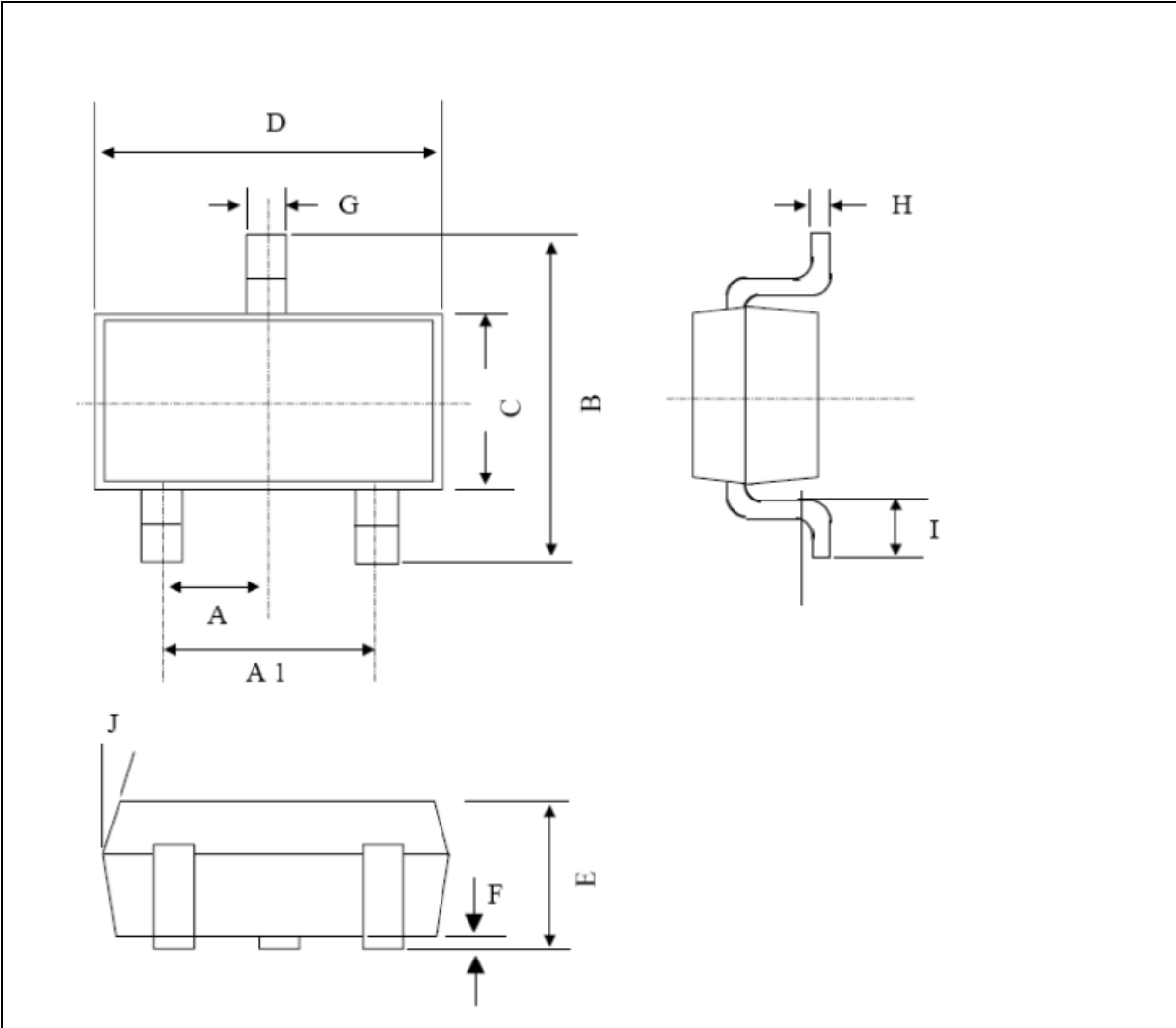
$dv/dt(c)$	Critical Rate-of-Rise of Commutation Voltage	$V_D = \text{Rated } V_{DRM}$ , $I_{TM} = .84\text{ A}$ , Commutating $di/dt = .3\text{ A/ms}$ , Gate Unenergized, $T_C = 50\text{ }^{\circ}\text{C}$	-	5.0	-	$\text{V}/\mu\text{s}$
$dv/dt$	Critical Rate of Rise of Off-State Voltage	$V_D = \text{Rated } V_{DRM}$ , $T_C = 110\text{ }^{\circ}\text{C}$ , Gate Open, Exponential Waveform	-	25	-	$\text{V}/\mu\text{s}$
$t_{gt}$	Gate controlled turn-on time	$V_D = \text{Rated } V_{DRM}$ , $I_{TM} = 1.0\text{ A pk}$ , $I_G = 25\text{ mA}$	-	2.0	-	$\mu\text{s}$

## 8. Electrical Characteristics Curve





9、Package outline(SOT-23-3L)



DIM	Inches		Milimeters		DIM	Inches		Milimeters	
	Min	Max	Min	Max		Min	Max	Min	Max
A	0.037BSC		0.95BSC		F	0.000	0.004	0.00	0.10
A1	0.074BSC		1.90BSC		G	0.012	0.020	0.30	0.50
B	0.089	0.100	2.25	2.55	H	0.003	0.006	0.08	0.15
C	0.059	0.067	1.50	1.70	I	0.012	0.020	0.30	0.50
D	0.114	0.122	2.9	3.10	J	5°	10°	5°	10°
E	0.039	0.045	0.90	1.15					